

ABSTRACT OF THE DISCLOSURE

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5 is disclosed in which wherein the edge portion of each of the gate electrodes overlaps the edge portion of each of the picture element electrodes to form an additional capacitor. The gate electrodes are made of tantalum, and a first insulating film of tantalum pentoxide and a second insulating film of silicon nitride are disposed in a gap between each of the gate electrodes and each of the picture element electrodes. This provides additional capacitors with a large capacity at a high yield, with little affect on other processes. ✓

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